Blue are new market stabilizing/positive leaning info. **Orange** are new neutral/negative info.

Device		Company	Production Profile	Comments
NAND		Overall NAND	3xxL products to ramp in 2025. Technology upgrades to manage supply.	
		Samsung	Vol.: 236L Ramp: 286L	- Upgrading Xi'an to V8/V9 - P4 NAND delayed to 2026, nodes transitions to manage supply.
		Kioxia	Vol: 218L	- Kitakami Fab 2 expected ops Sept. '25 after delays due to market conditions. - WD divested NAND into Sandisk; 2025 joint CapEx $1.9B (-25% vs. 2024)
		SK Hynix	Vol.: 321L	- Transitioning to 321L to manage supply leveraging 238L stacking technology
		Micron	Vol.: 232L	- Revised 2025 NAND CapEx down, using upgrades to manage supply
		YMTC	Vol: 232L	- Started ramping 294L in Q1'25; +15% capacity expansion targeted for E'26 - "All-Chinese" OEM pilot line planned in 2H'25
DRAM		Overall DRAM	HBM driving expanded DRAM spend to support AI; $4F^2$ development in progress	
		Samsung	Vol: 1b nm, Ramp: 1c nm	- Ongoing CapEx for expanding EUV capacity in Pyeongtaek P3 - E'25: Expected to add 1c capacity to P4 & migrate H17 from 1z → 1c
		SK Hynix	Vol: 1b nm, Ramp: 1c nm	- Accelerating M15x build-out, 2025 CapEx increase incl. Korea fab build - Focusing spend on high bandwidth memory (1b/1c node) to meet AI demand
		Micron	Vol: 1β nm Ramp: 1γ nm	- Targeting 2025 CapEx to be 30% of revenues, majority for DRAM/HBM - Additional CapEx announced (+$30B through 2045) for US mfg onshoring.
		ChangXin Mem. Tech. (CXMT)	1y ramp 1z delay	- Fab2 (Hefei) ramping; not on entities list but nearing BIS node limit - Delayed volume DDR5 to E'25; HBM development ongoing, expected 2026
		Other Memory	1x	- Nanya: new fab 2026 ramp expected - Winbond: slow Kaohsiung P1 (20K) ramp
Foundry/Logic	≤16nm	Foundry/Logic	Leading & trailing nodes investment planned. Fab utilization recovering.	
		TSMC	3nm	- FY'25 CapEx reiterated to $40B; indicated ~$40B spending in 2026+ - Total US investment $165B, AZ ramp accelerated again for strong demand - AZ (Fab1 4nm, 2025; F2 3nm, 2026; F3 2nm, 2027), Japan fab2 (6nm, 2027)
		Intel	4nm ≤14nm	- '25/'26 CapEx cut; further slowing Ohio fab; cancelled Germany fab. - AZ 18A ramp expected E'25
		Samsung	3nm GAA	- Reduced CapEx in '25. Delayed Taylor TX completion for market conditions. - Yongin fab complex planned, target building 5 logic fabs in 20 years ($230B)
		GlobalFoundries	14nm	- Malta new fab planned, timing TBD.
		SMIC	<14nm	- Delivering 7/5nm to Chinese chipmakers to circumvent US restrictions
	≥20nm	TSMC	22/28nm 12/16nm	- Japan fab revised timeline to realign target technologies to market. - Dresden JV fab (groundbreaking Aug'24, ramp 2027-end)
		UMC	28nm	- 2025 CapEx revised to ~$1.8B, Singapore production pushed to 2026
		SMIC	28nm	- Continuing high spending level with ~$7B forecast for 2025
		Powerchip	>28nm	- Ramp of new Tongluo (+19K); Technology license sale to Tata (India)
		GlobalFoundries	28nm, FDSOI	- Announced 2x capacity expansion of Dresden fab to be completed by 2032. - Collaboration with ST put on hold.
		Other	>28nm	- US: TI announced 2 additional fabs for Sherman (SM3&4) to long-term plan. - China: CanSemi (Guangzhou, +40K wmp), Hua Hong (Wuxi, $6.7B +30K), Wingsky (Shanghai, 45K), Zensemi (MEMS, Quangshou), CR Micro (Shenzhen) - Japan: Toshiba (P2 '26), slowed/inactive: Renesas; Rohm, Sanken, Sony. - Europe: ST (Crolles on hold); Infineon (Dresden, 2026) - India: Tata (2026, building fab exec team & OSAT M&A/partners)
Packaging		TSMC	-	- $4-8B (10-20% CapEx), incl. expanding CoWoS capacity to support AI demand - US Adv. packaging fabs (constr. 2027)
		Intel		- Consolidating sites (closing Costa Rica); canceled Poland plan (2027).
		GlobalFoundries		- Adding adv. pkg & test expansion to Malta
		SK Hynix		- HBM fab in Indiana (2028)